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NSBC123TDP6

Dual NPN Bias Resistor Transistors R1 = 2.2 k Ω , R2 = ∞ k Ω

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q1 and Q2, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	۱ _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	12	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

Device	Package	Shipping [†]
NSBC123TDP6T5G	SOT-963	8,000 / Tape & Reel

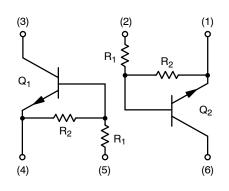
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



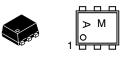
ON Semiconductor®

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PIN CONNECTIONS



MARKING DIAGRAMS



SOT-963 CASE 527AD

A = M =

Specific Device CodeDate Code*

*Date Code orientation may vary depending upon manufacturing location.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
ISBC123TDP6 (SOT-963) One Junction Heated			
Total Device Dissipation T _A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	PD	231 269 1.9 2.2	mW mW/°C
Thermal Resistance, (Note 1) Junction to Ambient (Note 2)	R _{0JA}	540 464	°C/W

NSBC123TDP6 (SOT-963) Both Junction Heated (Note 3)

$ \begin{array}{l} \mbox{Total Device Dissipation} \\ T_A = 25^\circ C & (Note 1) \\ (Note 2) \\ \mbox{Derate above } 25^\circ C & (Note 1) \\ (Note 2) \end{array} $	P _D	339 408 2.7 3.3	mW mW/°C
Thermal Resistance,(Note 1)Junction to Ambient(Note 2)	$R_{ hetaJA}$	369 306	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

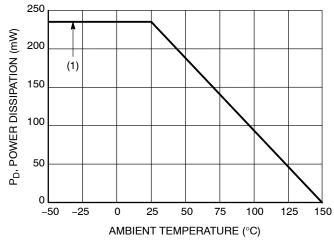
FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.
 Both junction heated values assume total power is sum of two equally powered channels.

NSBC123TDP6

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, common for Q_1 and Q_2 , unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	_	_	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I _{CEO}	-	_	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0 \text{ V}, I_C = 0$)	I _{EBO}	_	-	4.0	mAdc
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V _(BR) CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 4) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V _{(BR)CEO}	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	160	350	-	
Collector–Emitter Saturation Voltage (Note 4) $(I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA})$	V _{CE(sat)}	-	-	0.25	Vdc
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μ A)	V _{i(off)}	-	0.6	-	Vdc
Input Voltage (on) (V _{CE} = 0.2 V, I _C = 10 mA)	V _{i(on)}	-	0.9	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	_	_	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.25 V, R _L = 1.0 kΩ)	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	1.5	2.2	2.9	kΩ
Resistor Ratio	R ₁ /R ₂	-	-	-	

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

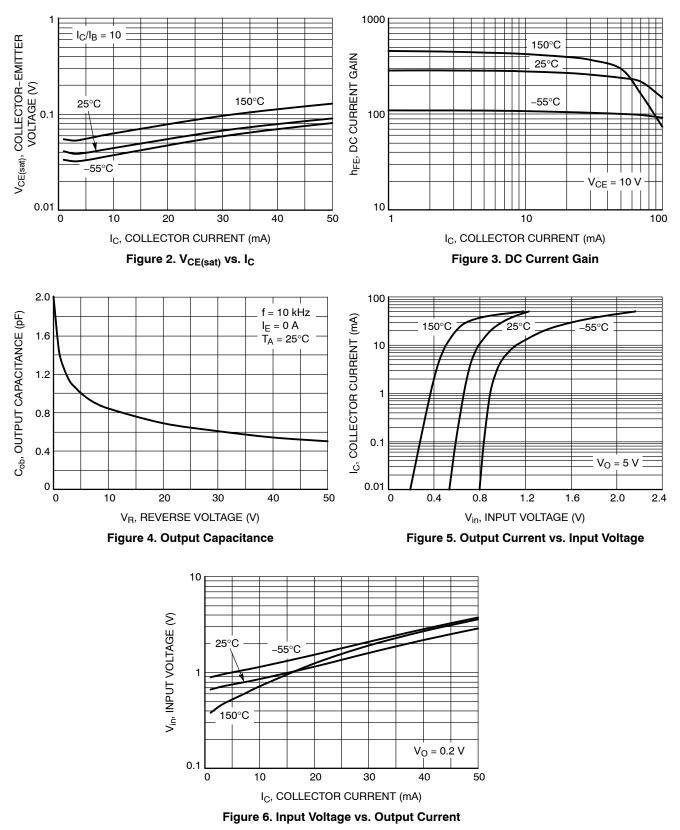


(1) SOT-963; 100 mm², 1 oz. copper trace

Figure 1. Derating Curve

NSBC123TDP6

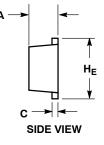
TYPICAL CHARACTERISTICS NSBC123TDP6

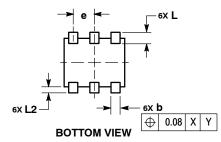


PACKAGE DIMENSIONS

SOT-963 CASE 527AD ISSUE E





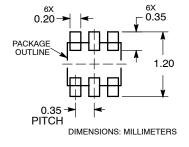


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.34	0.37	0.40
b	0.10	0.15	0.20
С	0.07	0.12	0.17
D	0.95	1.00	1.05
Е	0.75	0.80	0.85
е	0.35 BSC		
ΗE	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

RECOMMENDED MOUNTING FOOTPRINT



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